

FIG. 1A

PRIOR ART

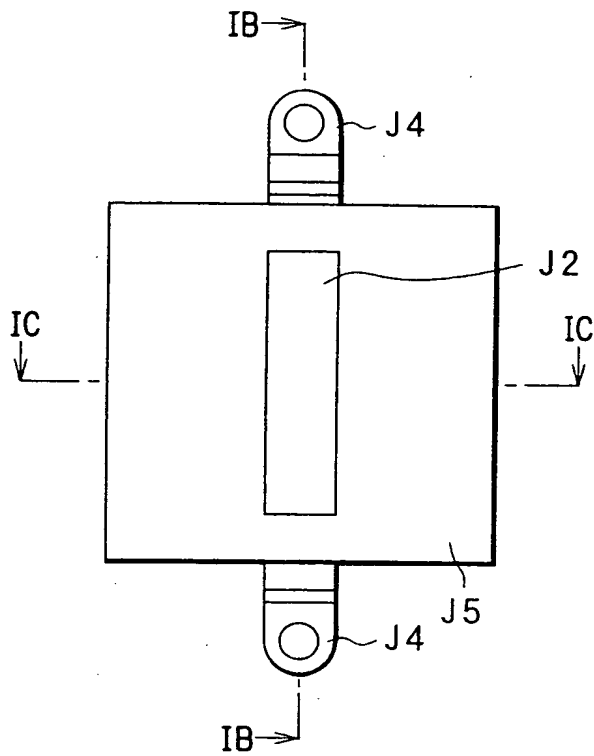


FIG. 1B

PRIOR ART

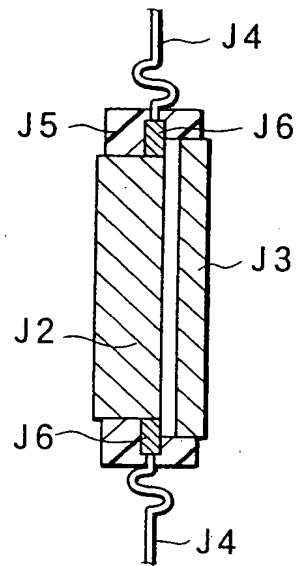


FIG. 1C

PRIOR ART

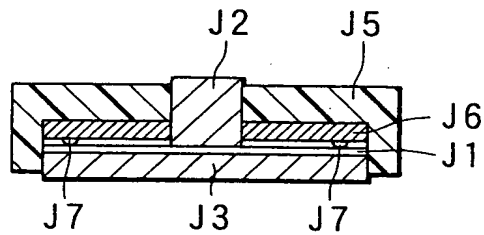


FIG. 2A

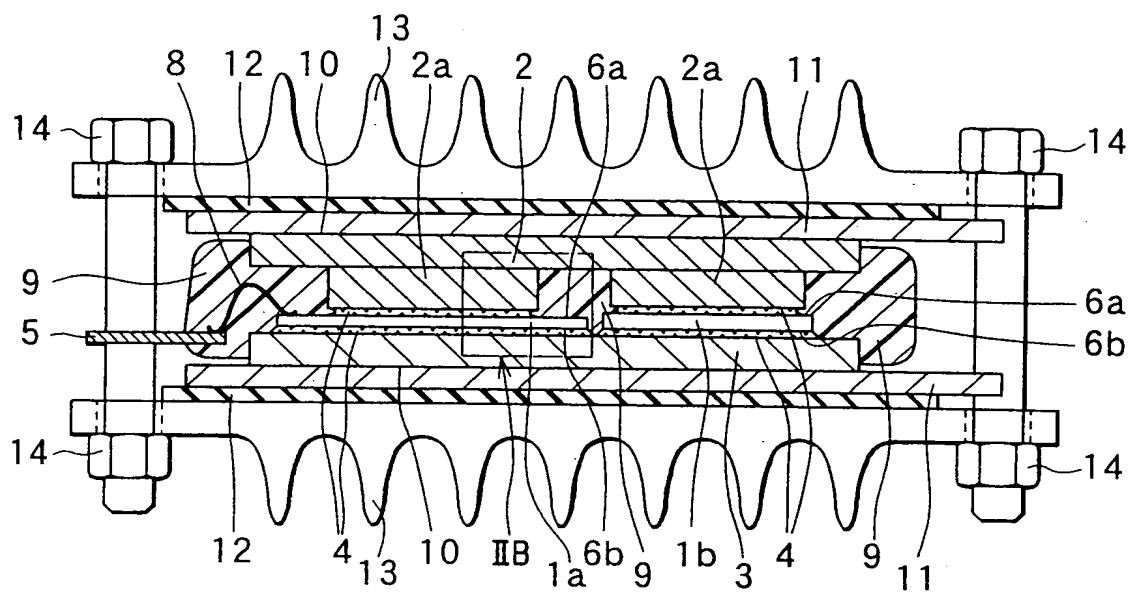


FIG. 2B

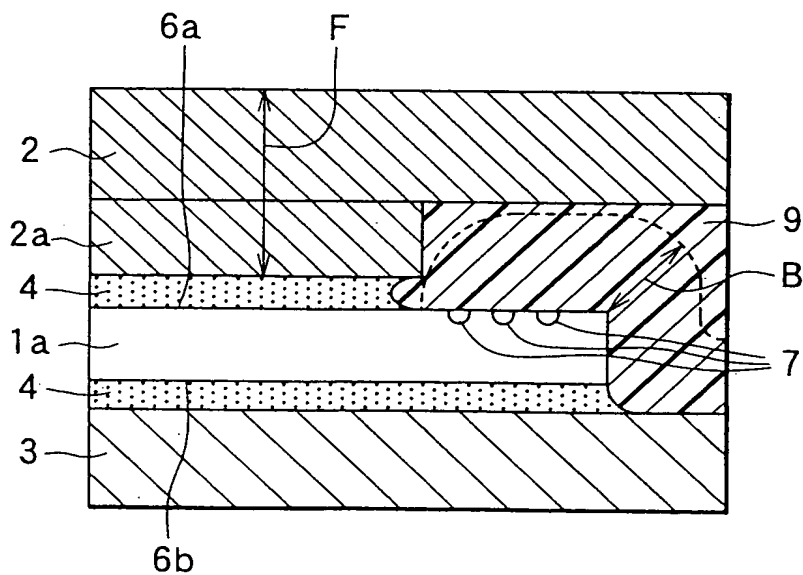


FIG. 3

NAME OF METAL	CHEMICAL COMPOSITION (%)													
	Fe	Zn	P	Ni	Si	Sn	NiB	Mn	Mg	Cr	Ti	B	Cu	Al
METAL a	2.3	0.1	0.03										REMAIN.	
METAL b	2.4	0.12	0.03										REMAIN.	
METAL c				3.0	0.7								REMAIN.	
METAL d	1.5	0.5				0.5							REMAIN.	
METAL e	1.0	0.05	0.1			1.0							REMAIN.	
METAL f	0.75		0.03			1.25							REMAIN.	
METAL g	0.05 0.15		0.025 0.040										REMAIN.	
METAL h	0.05 0.4		0.05 0.1			0.05 0.2	0.05 0.45						REMAIN.	
METAL i			0.15 OR LOWER	0.1 0.4		1.7 2.3							REMAIN.	
METAL j		0.2 0.35		3.0 3.4	0.6 0.75	1.0 1.5							REMAIN.	
METAL k	0.12 1.0	0.03 0.1			0.1 1.0			0.02 0.05	0.02 0.05		0.02 0.05		0.03 0.2	REMAIN.
METAL l	0.5	0.1			0.3 0.7			0.05	0.35 0.5	0.03		0.06	0.1	REMAIN.

FIG. 4A

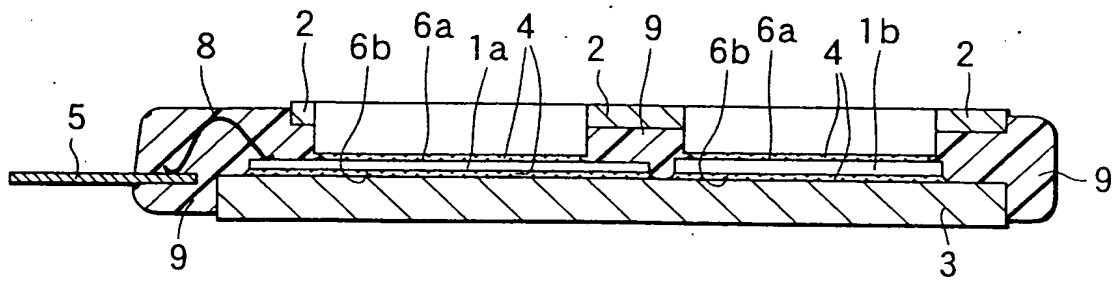


FIG. 4B

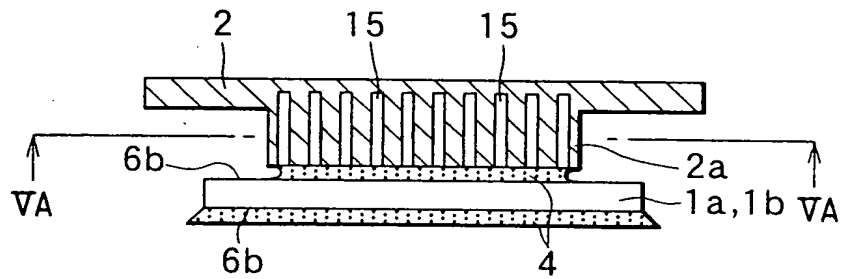


FIG. 4C

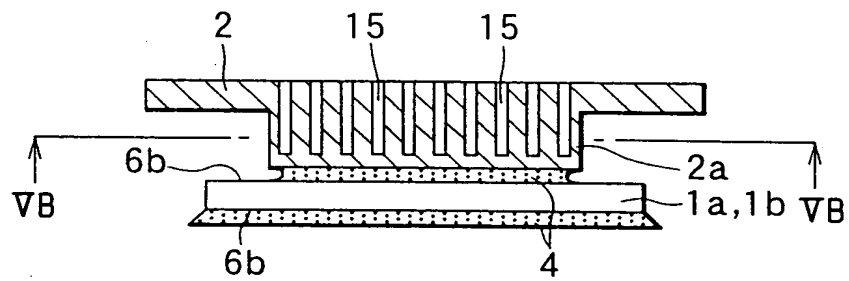


FIG. 4D

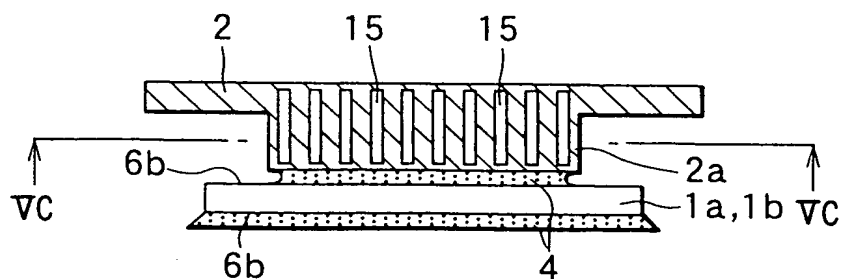


FIG. 5A

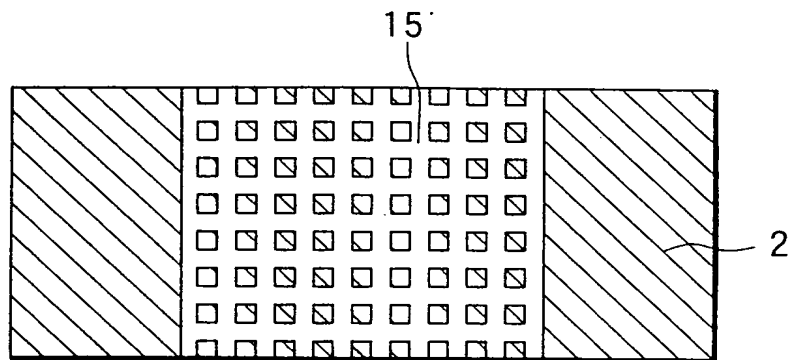


FIG. 5B

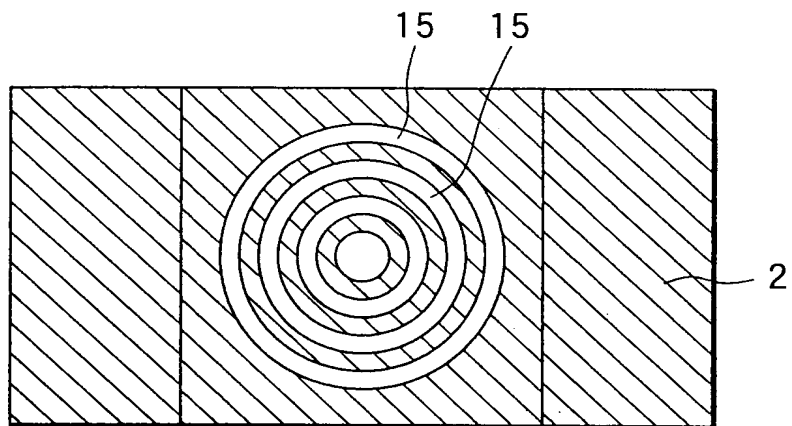


FIG. 5C

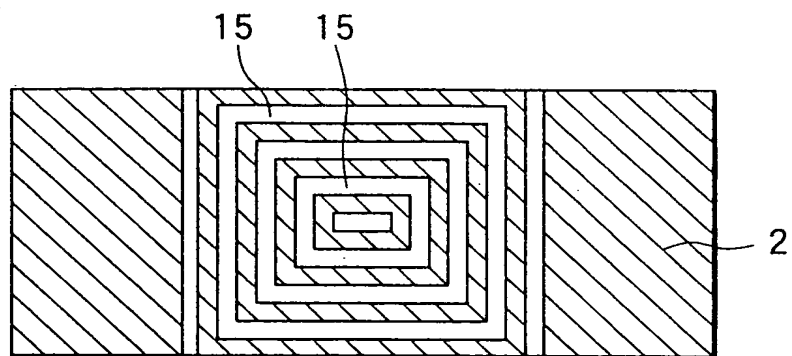


FIG. 6

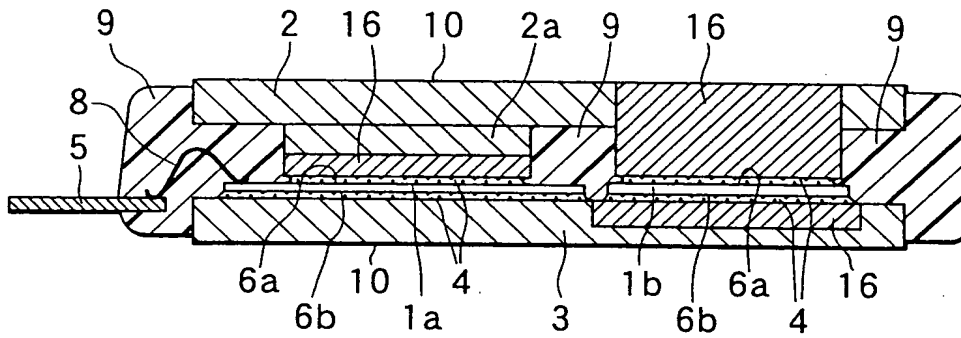


FIG. 7

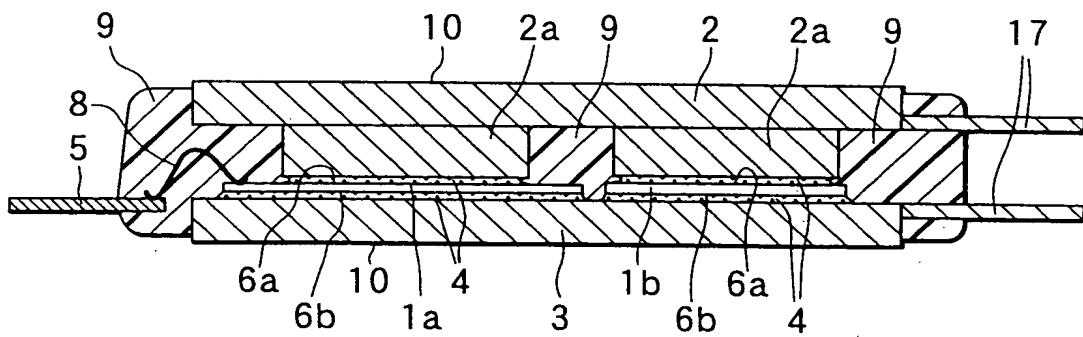


FIG. 8A

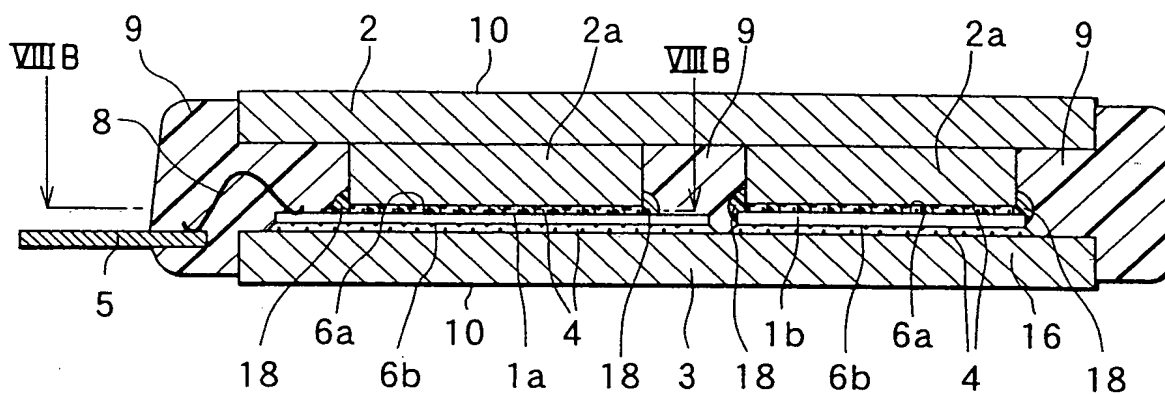


FIG. 8B

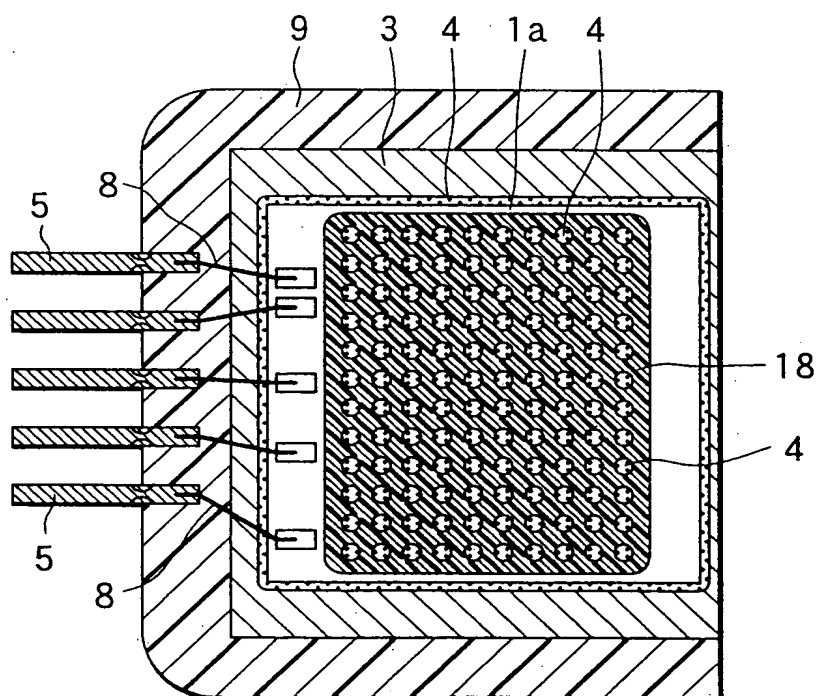


Fig. 1 is a cross-sectional view of a device for processing a workpiece. A workpiece 1 is held between two jaws 2 and 3 of a clamping device 4. A tool 5 is positioned to machine the workpiece. The device includes a base 10 and a support 9. Dimensions 19 and 20 are indicated. Labels 6a, 6b, 1a, and 4 are also present.

A cross-sectional view of a multi-layered structure. The structure consists of several layers: a top layer (2) with diagonal hatching, a layer (4) with a dotted pattern, a central layer (7) with a solid white fill, and a bottom layer (3) with diagonal hatching. A central cavity (1a) is formed by the removal of material from the central layer (7). The cavity is bounded by a top surface (20) and a bottom surface (9). The top surface (20) is a horizontal line. The bottom surface (9) is a horizontal line. The side walls of the cavity are formed by the central layer (7). The top layer (2) and bottom layer (3) are shown as continuous across the top and bottom of the structure. The layer (4) is shown as a thin layer between the top and bottom layers (2) and (3). The central layer (7) is shown as a thick layer in the center of the structure. The cavity (1a) is shown as a large, irregularly shaped void in the center of the structure.

FIG. 10

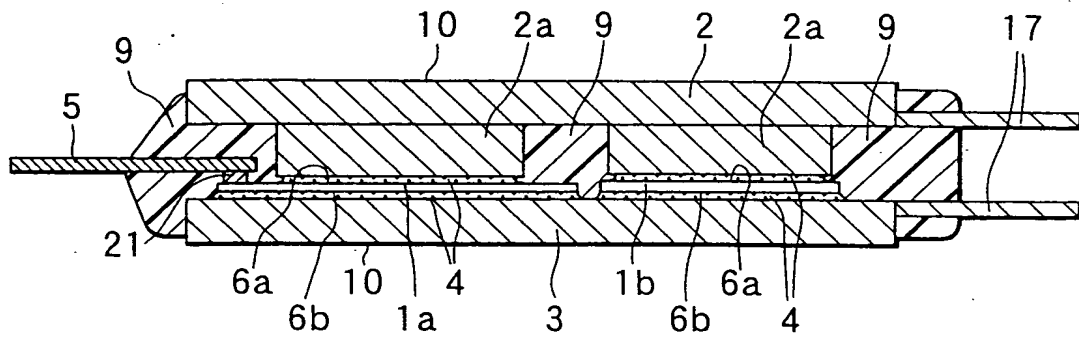


FIG. 11

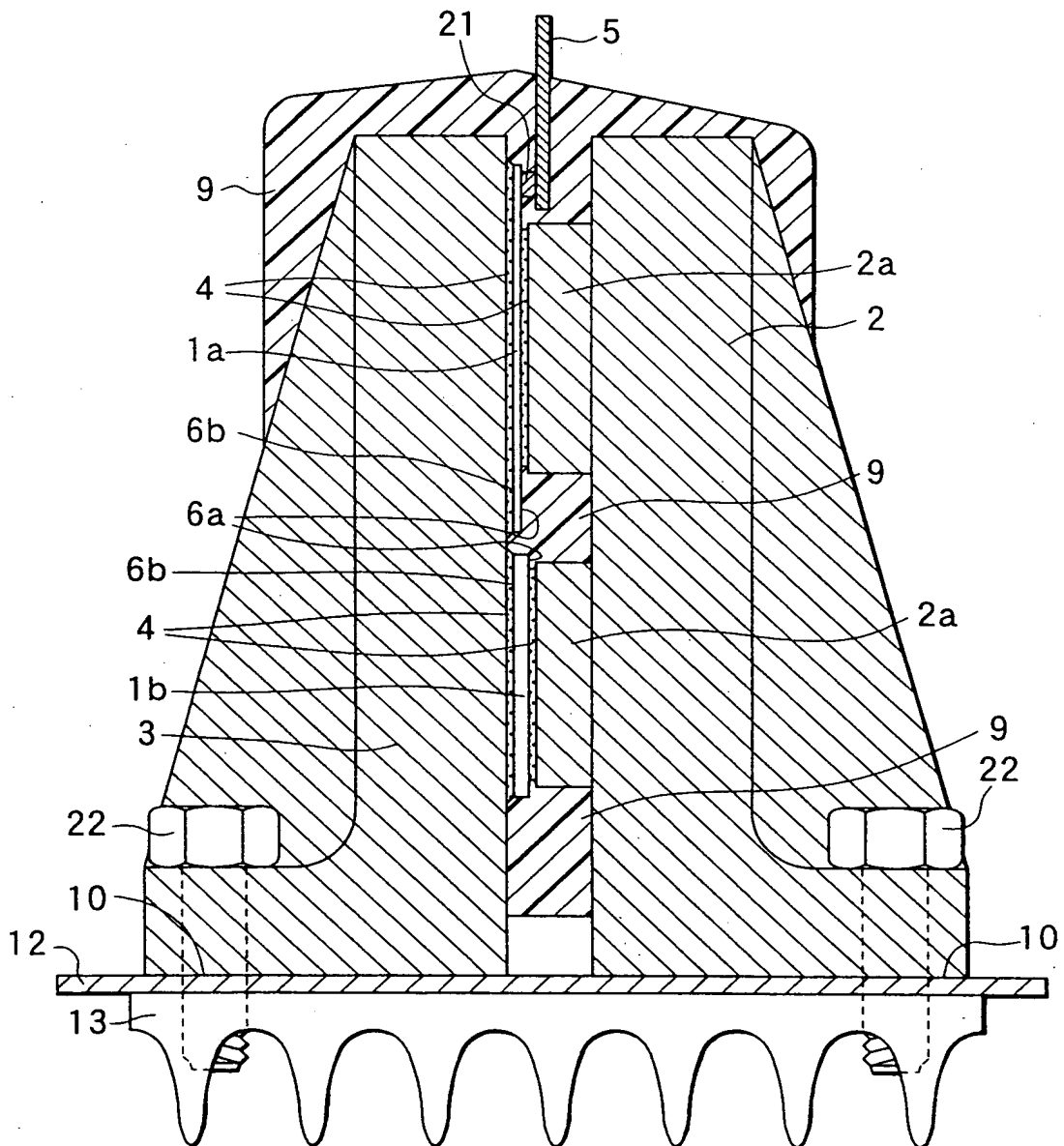


FIG. 12

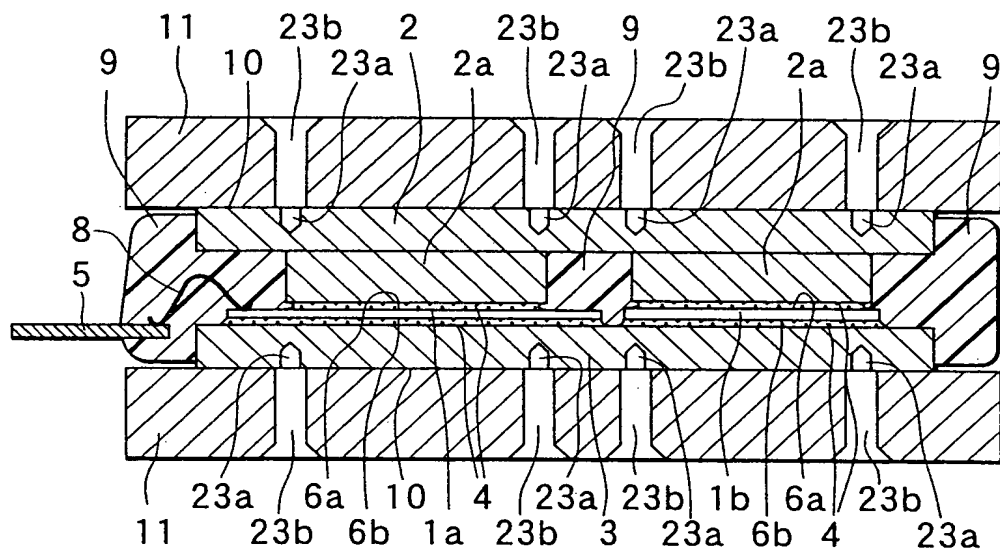


FIG. 13

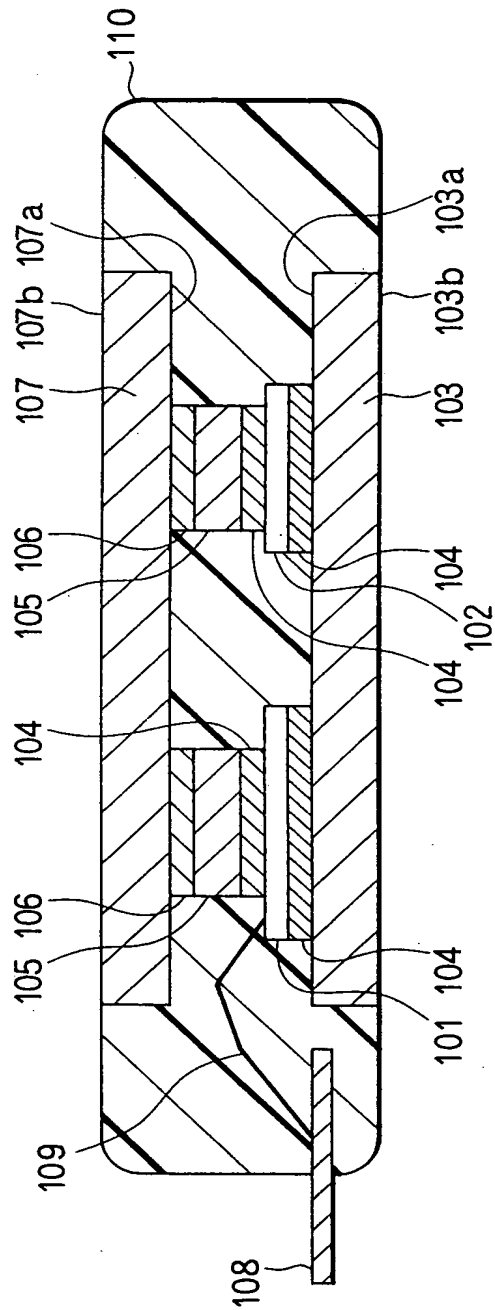


FIG. 14A

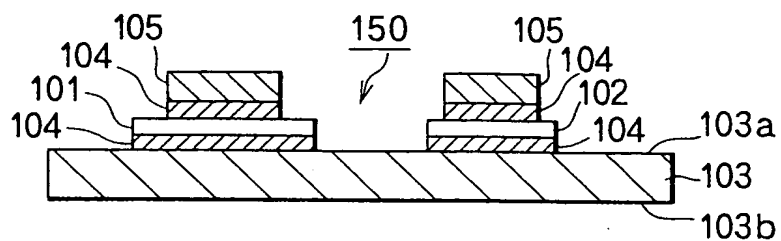


FIG. 14B

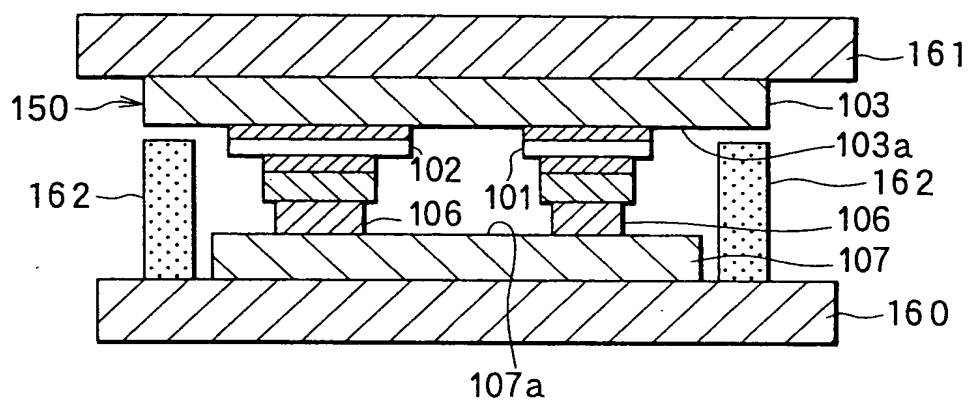


FIG. 14C

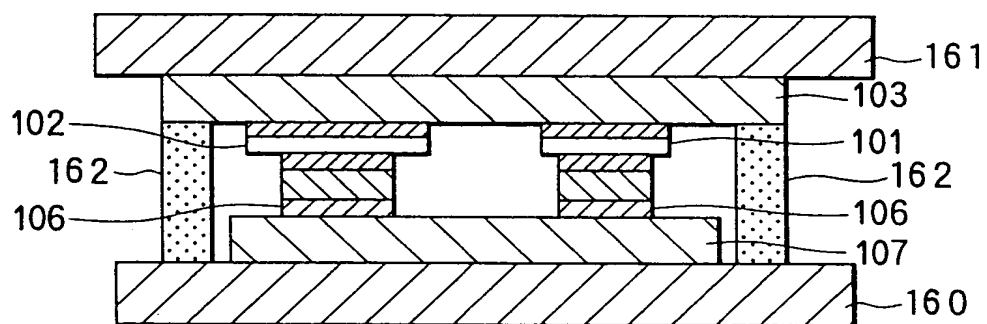


FIG. 15

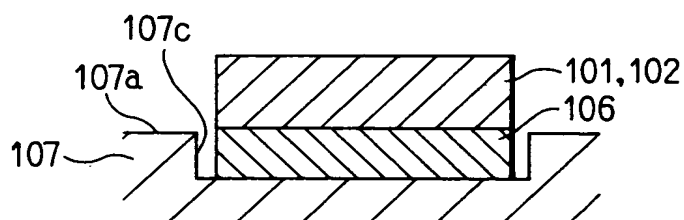


FIG. 16

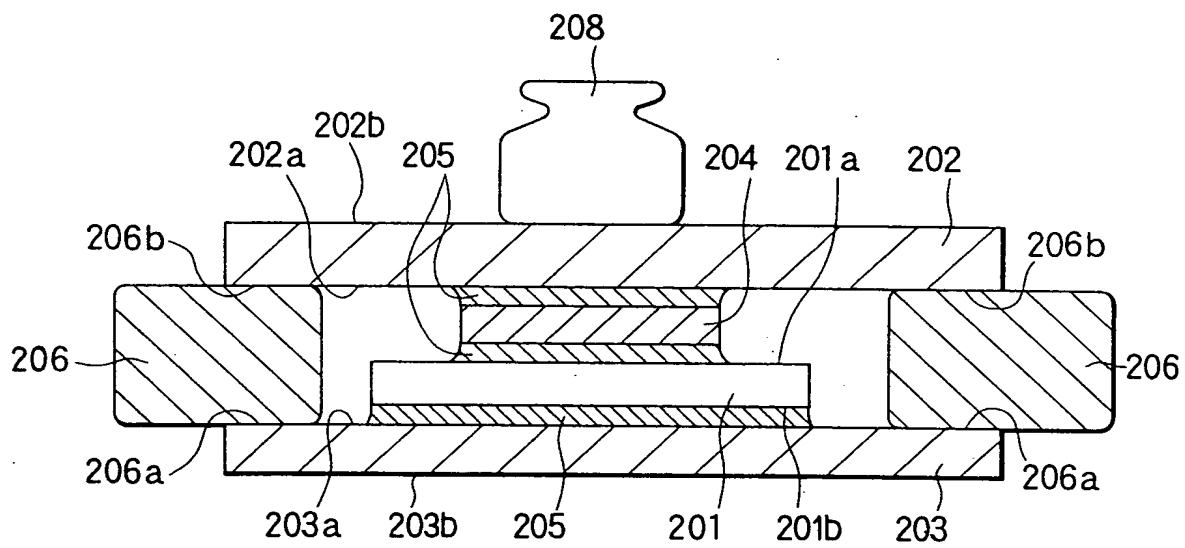


FIG. 17

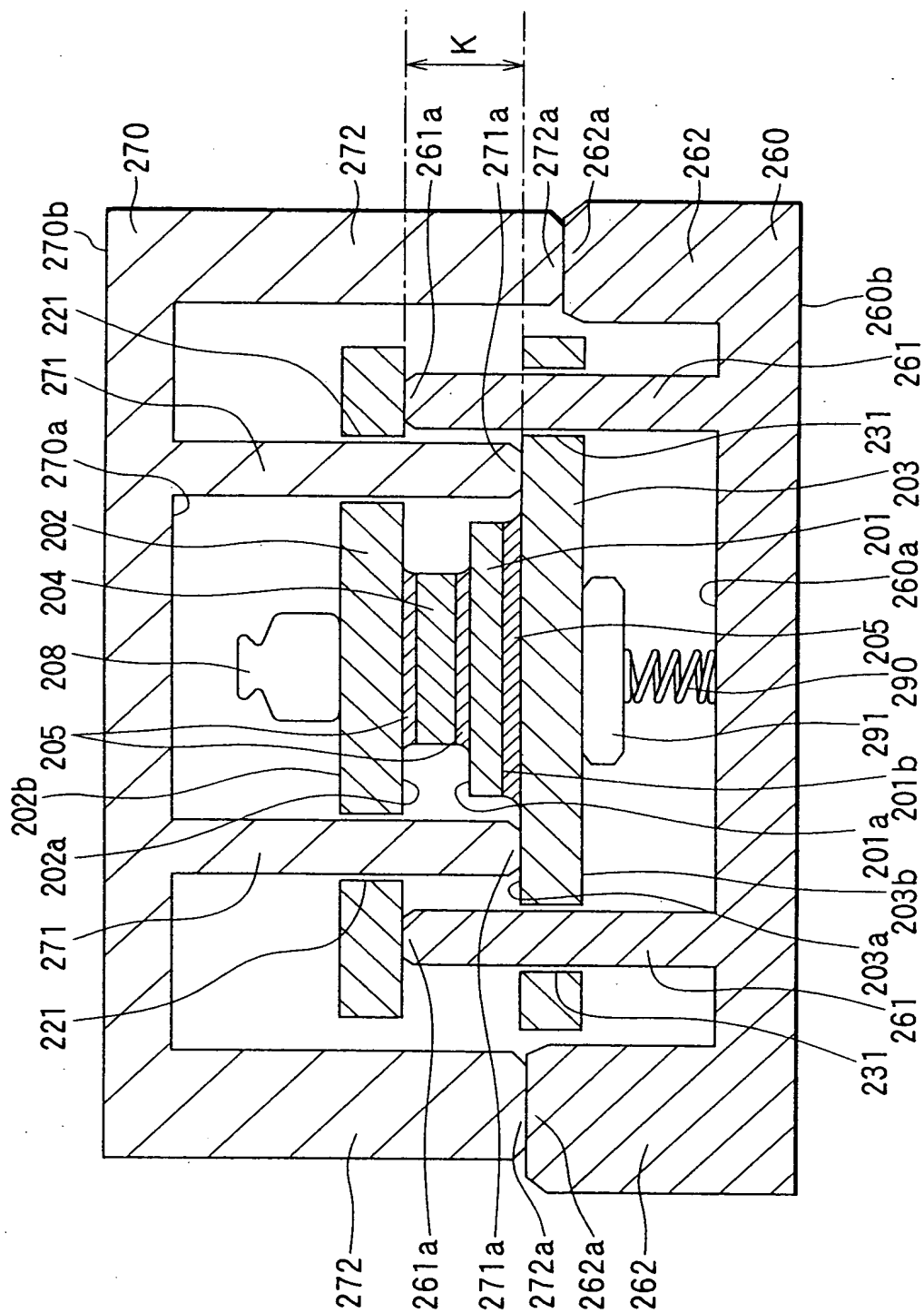


FIG. 18

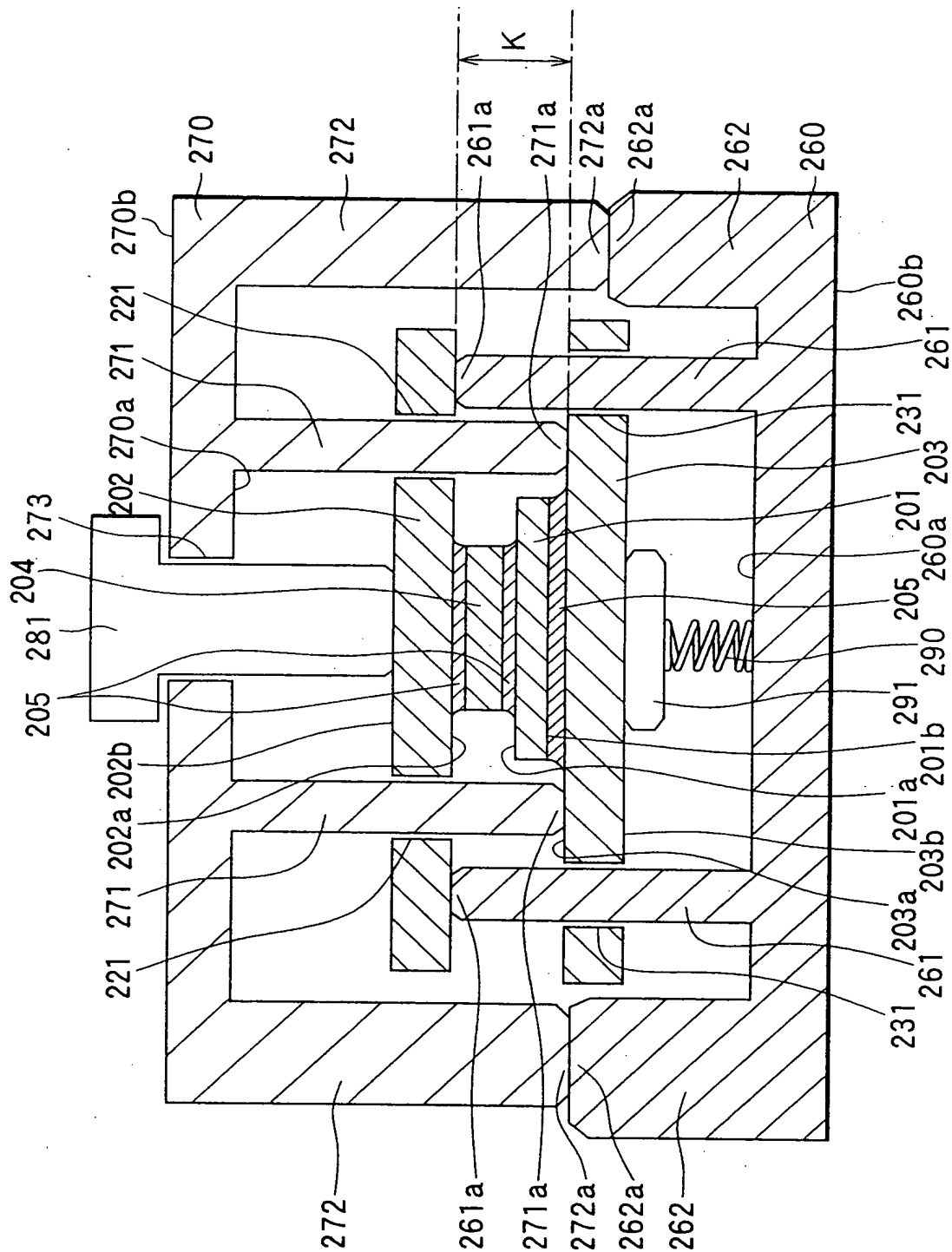


FIG. 19

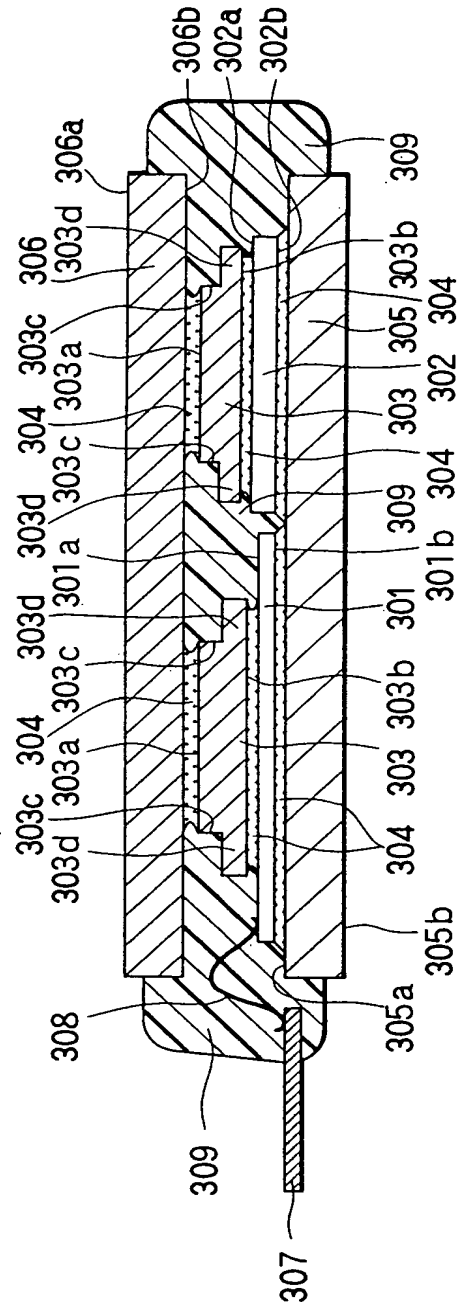


FIG. 20A

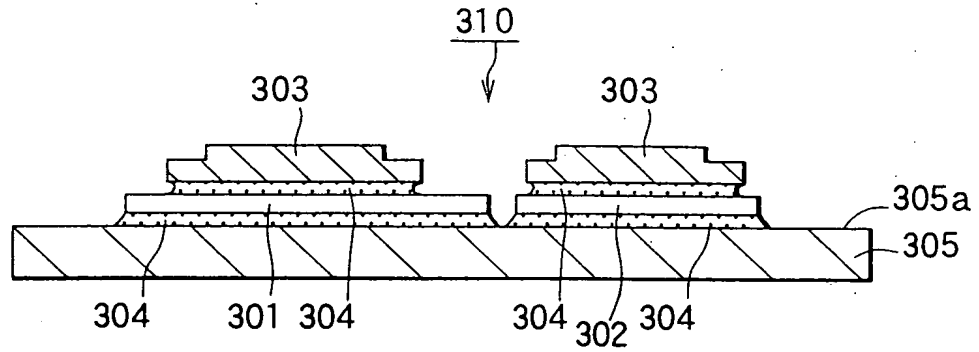


FIG. 20B

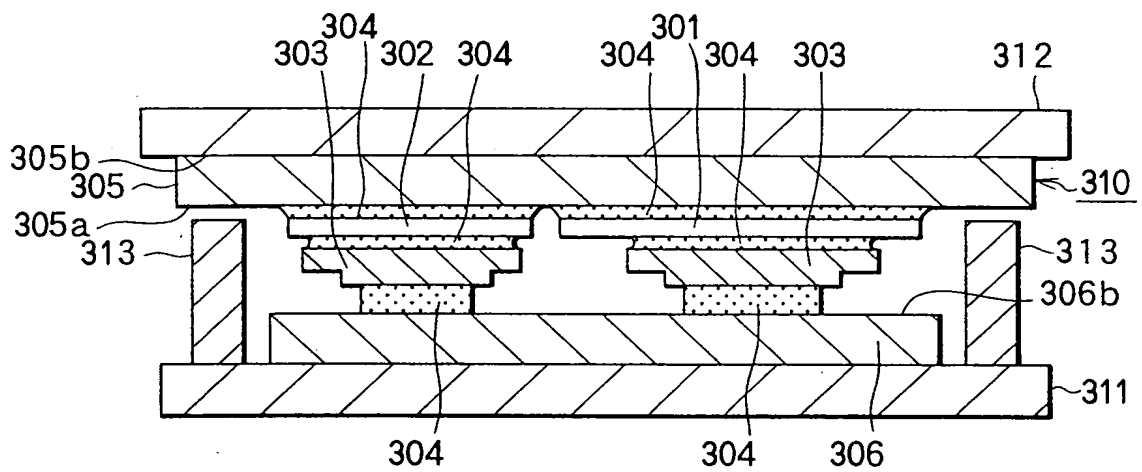


FIG. 20C

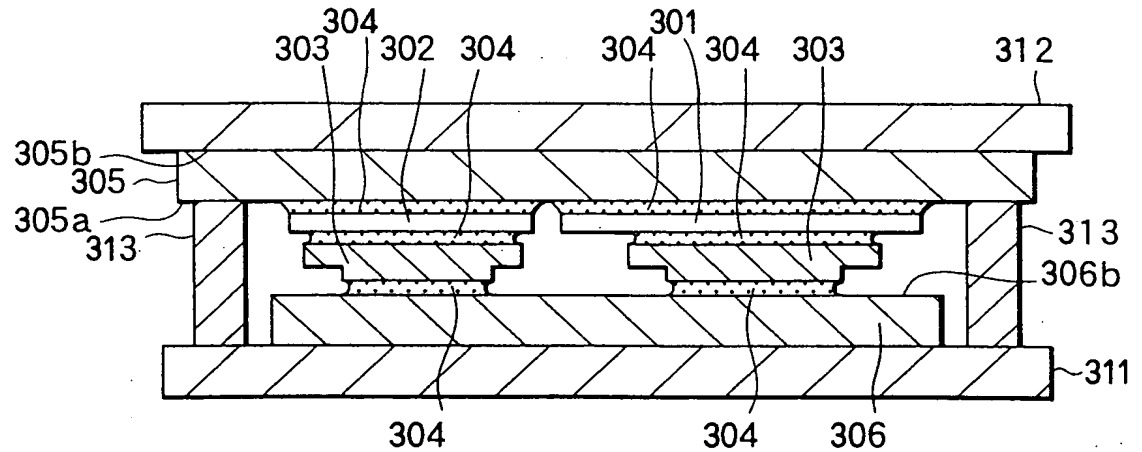


FIG. 21

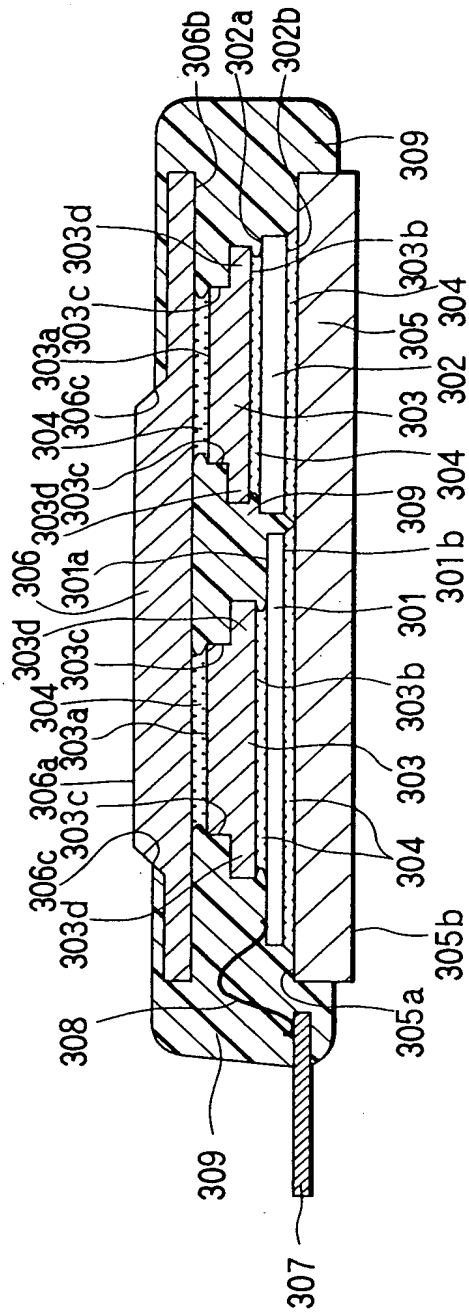


FIG. 22

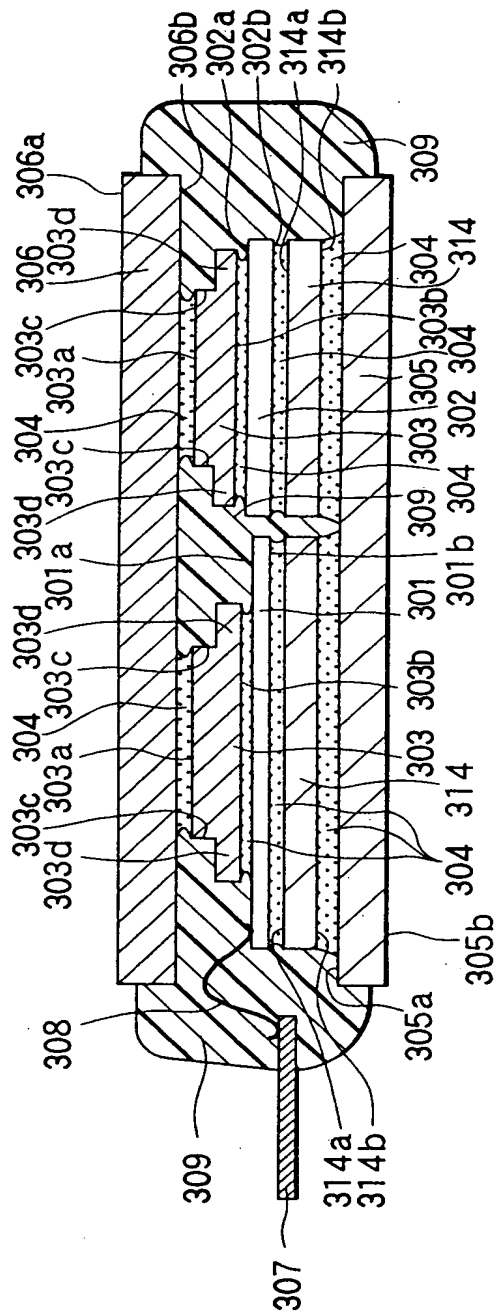


FIG. 23

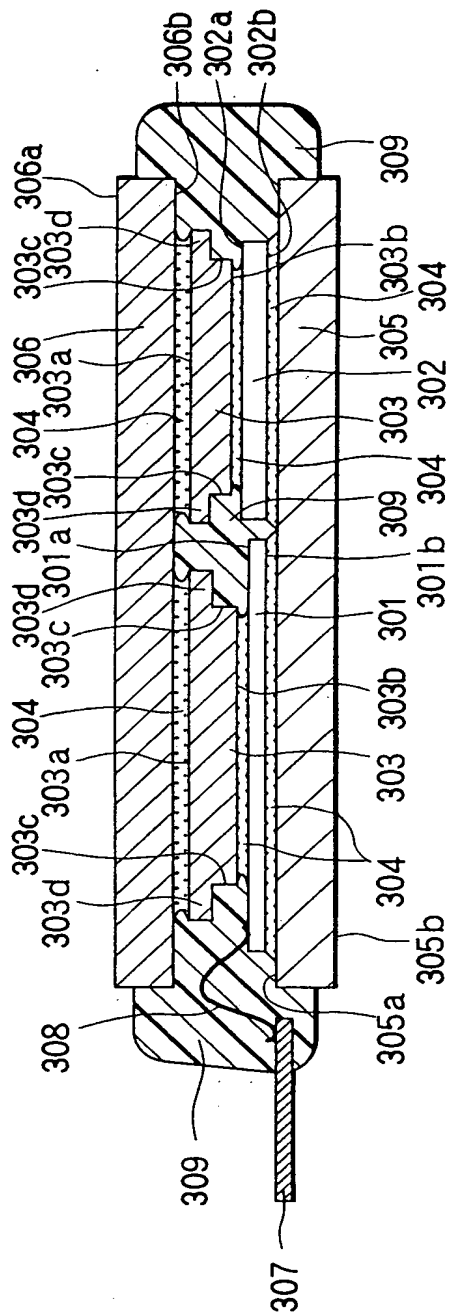


FIG. 24

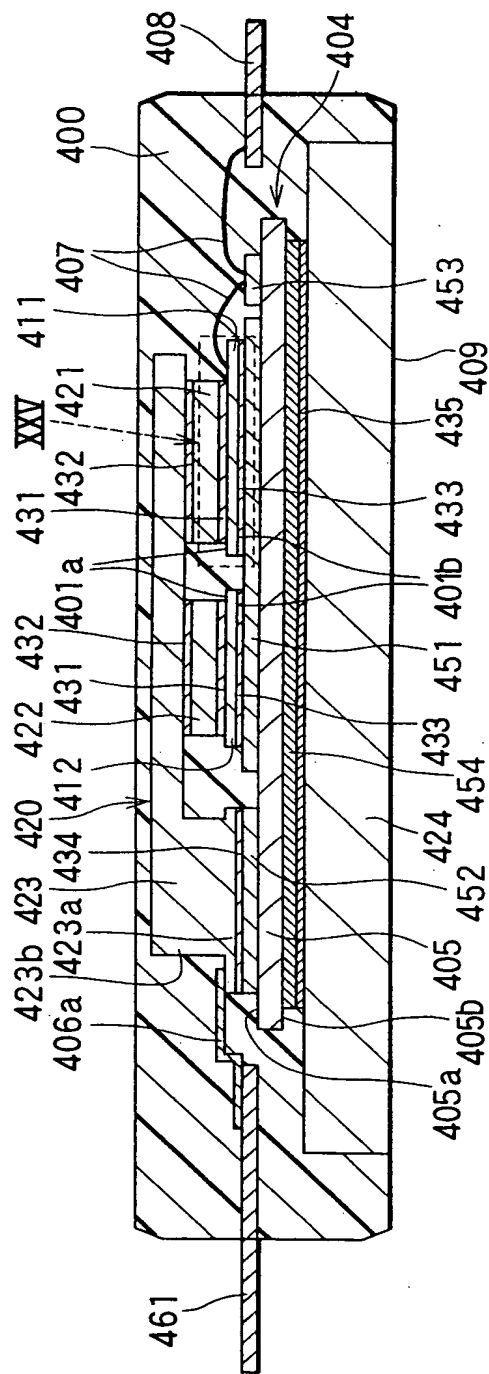


FIG. 25

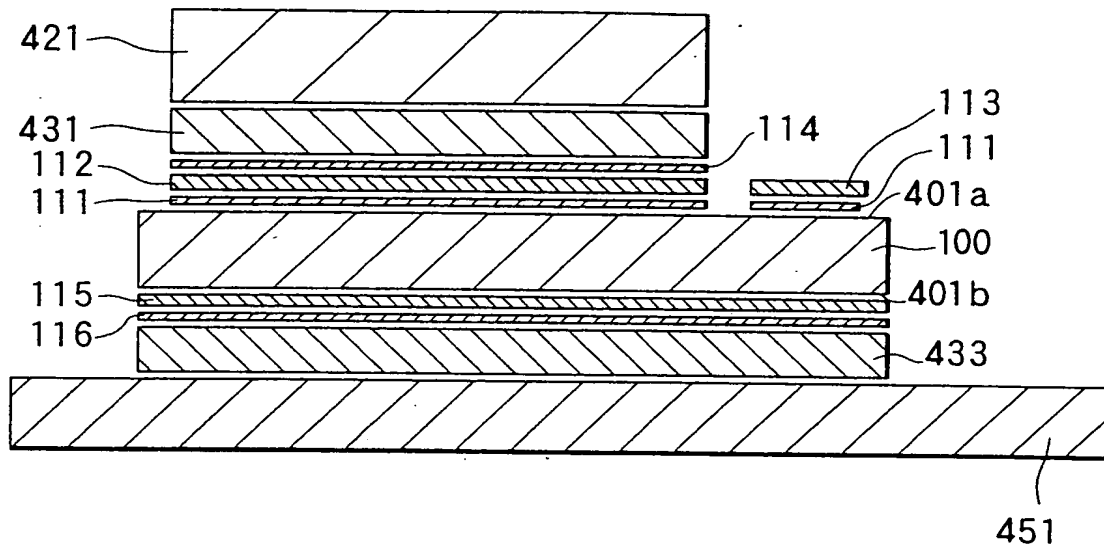


FIG. 26

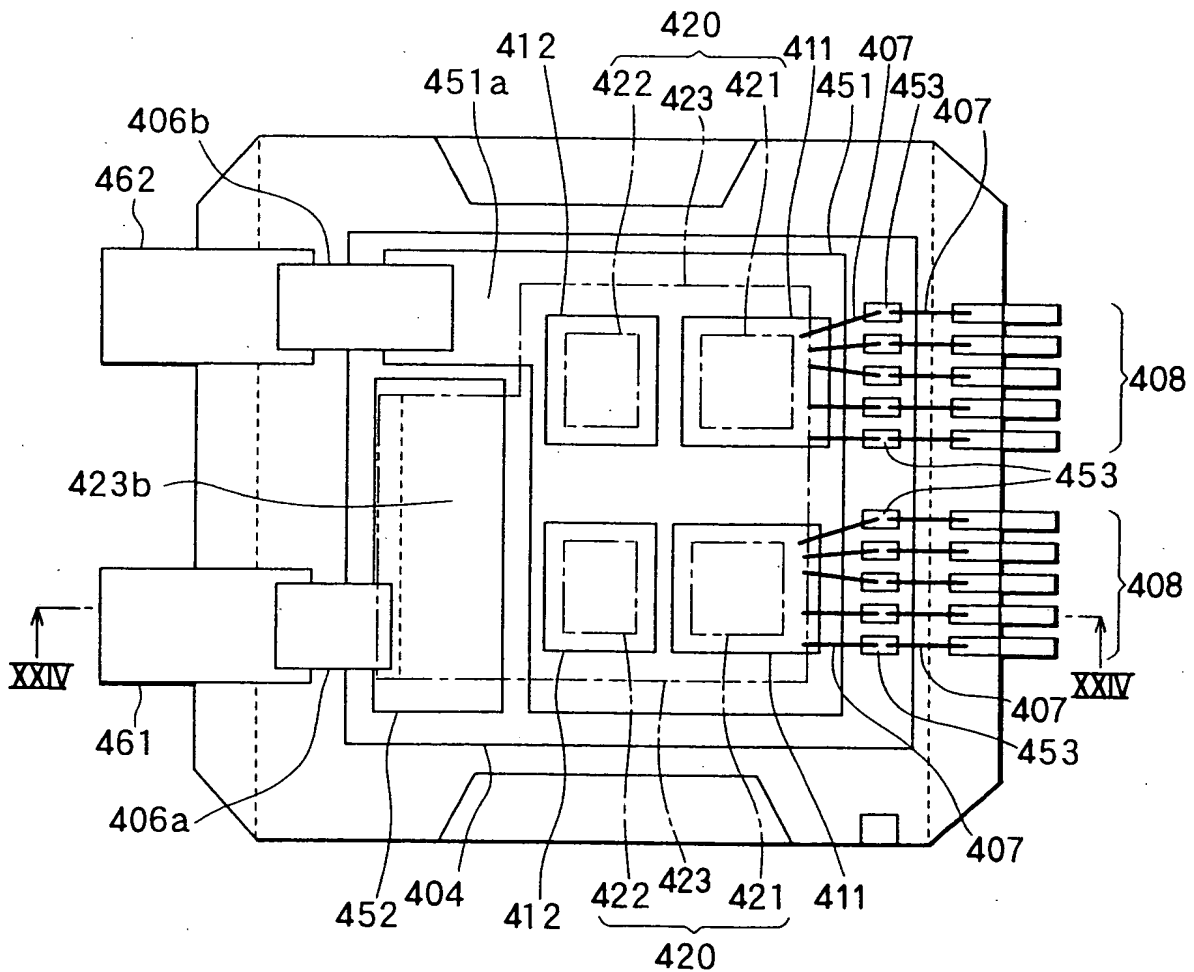


FIG. 27

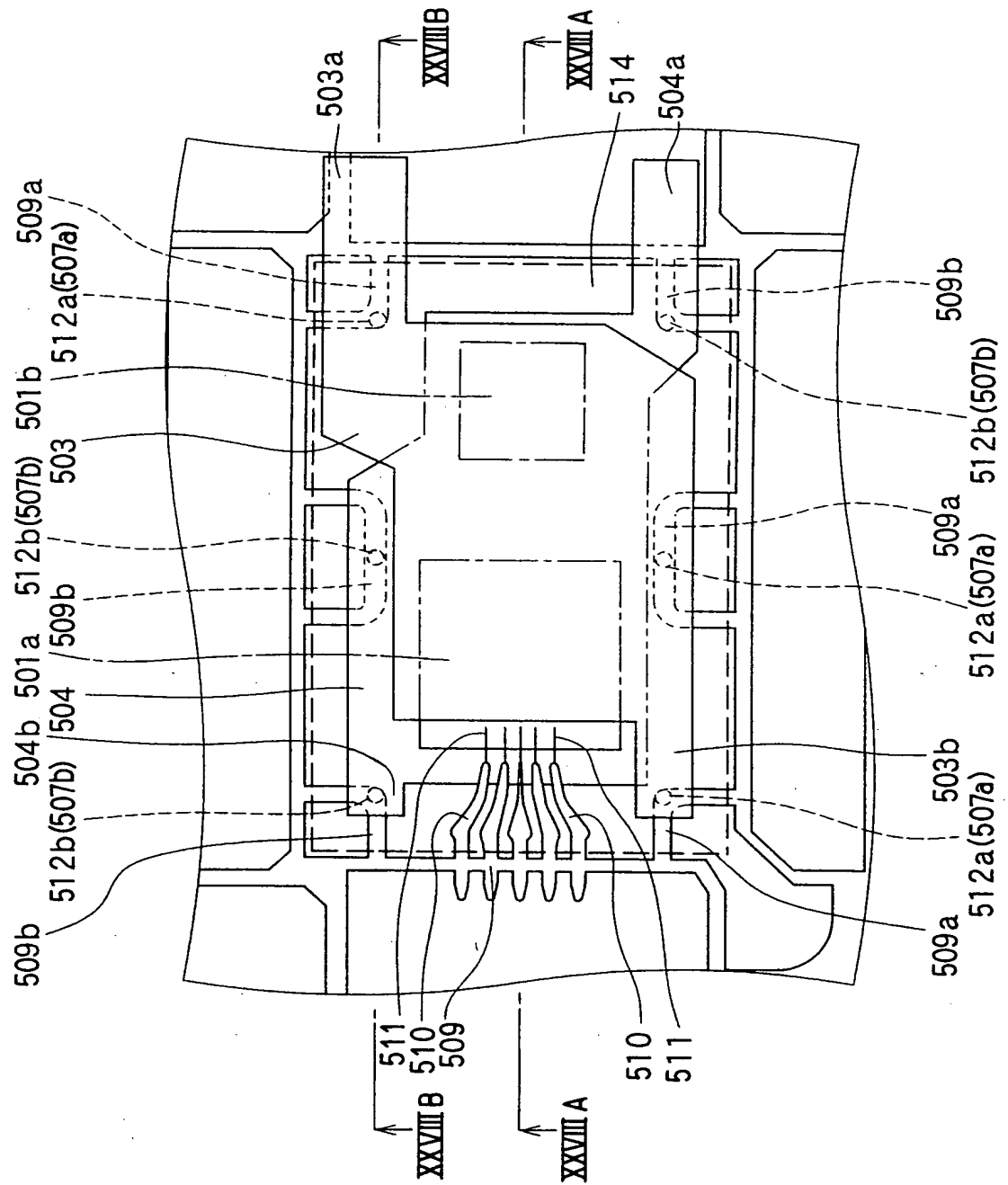


FIG. 28A

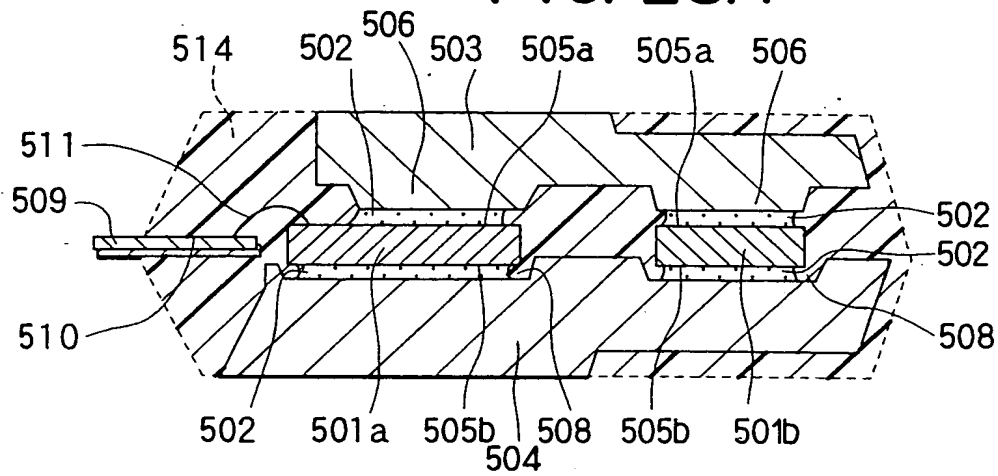


FIG. 28B

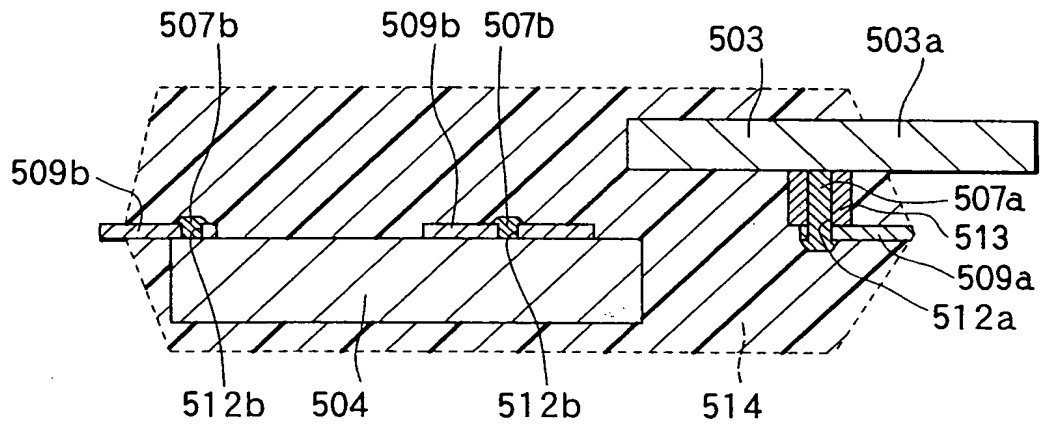


FIG. 29

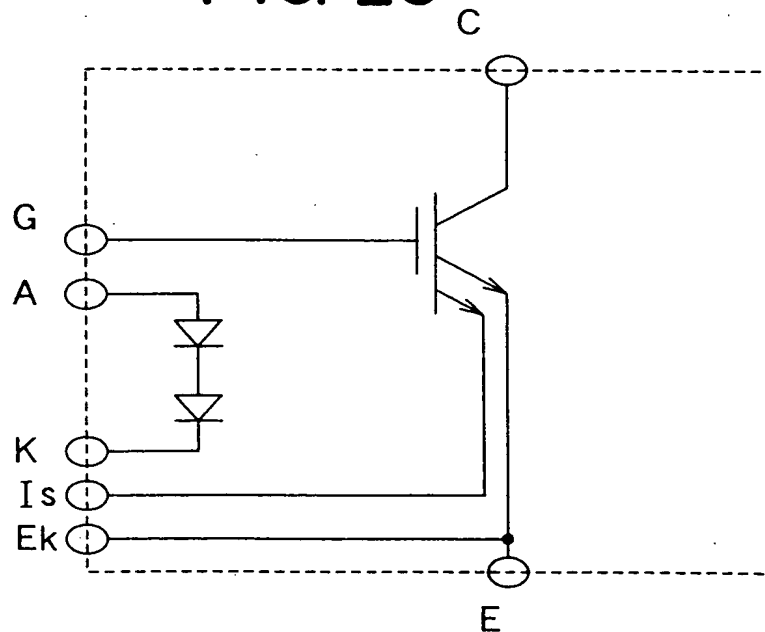


FIG. 30A

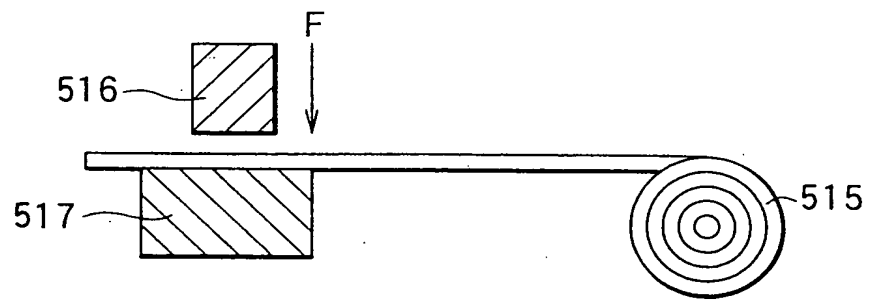


FIG. 30B

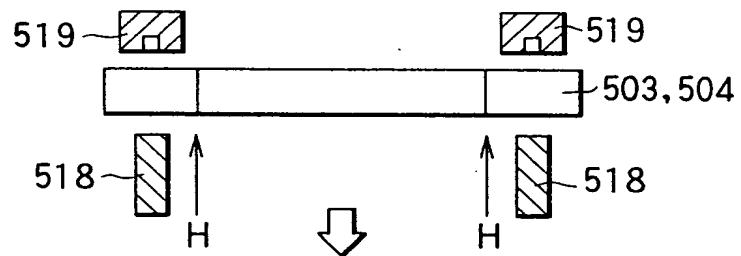


FIG. 30C

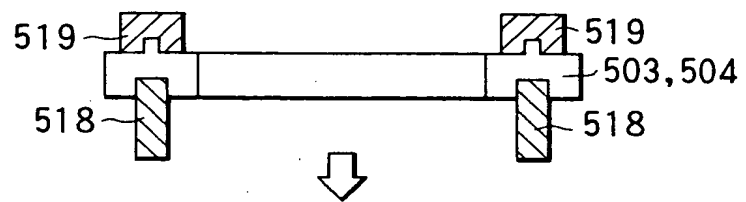


FIG. 30D



Fig. 10 is a cross-sectional view of a semiconductor device. It shows a substrate 504 with a series of recessed regions 508. A layer 502 is deposited over the substrate, filling the recessed regions 508. On top of layer 502, there are two main rectangular blocks 501a and 501b. Layer 505a is a thin layer on top of 501a and 501b. Layer 505b is a thin layer on top of 501a and 501b. A layer 507b is on top of 501a and 501b. A layer 509b is on top of 501a and 501b. A layer 509a is on top of 501a and 501b. A layer 512b is on top of 501a and 501b. A layer 512a is on top of 501a and 501b. A layer 513 is on top of 501a and 501b. A layer 507a is on top of 501a and 501b.

This diagram shows a cross-sectional view of a second embodiment of the semiconductor device. It features a substrate 503 with a central layer 504. On top of the substrate, there are two raised regions 507a and 507b. Between these regions and extending beyond them is a layer 509. On the top surface of layer 509, there are two sets of contacts or openings labeled 512a and 512b.

FIG. 33

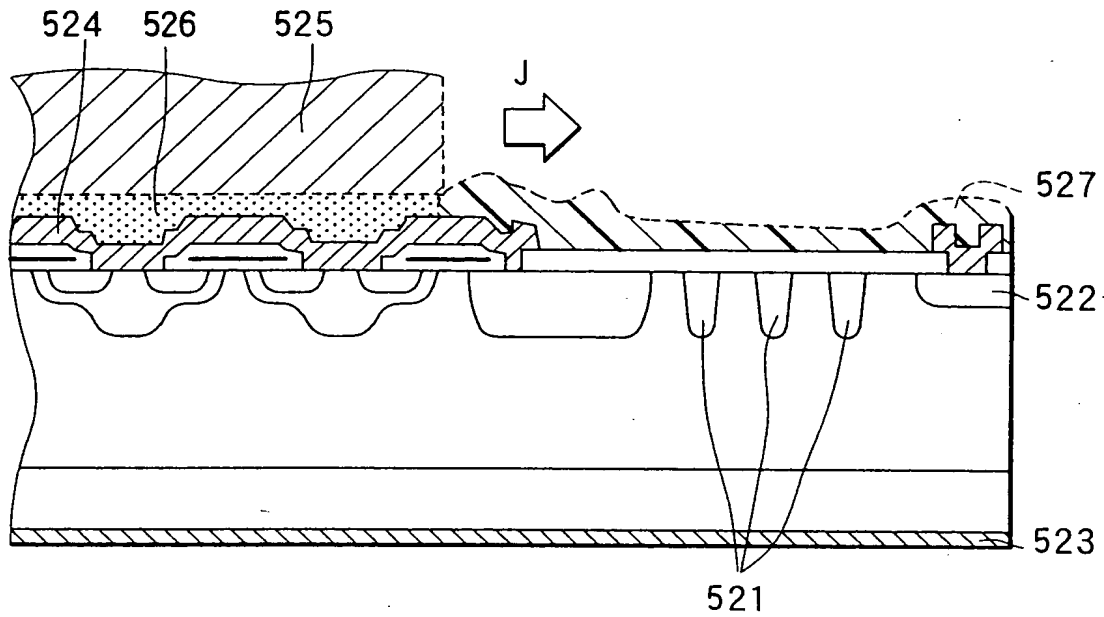


FIG. 34

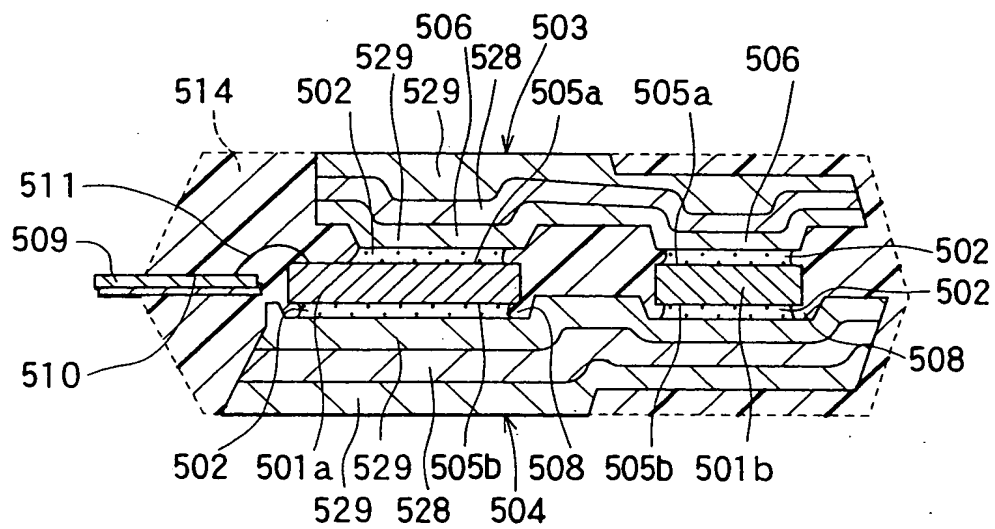


FIG. 35A

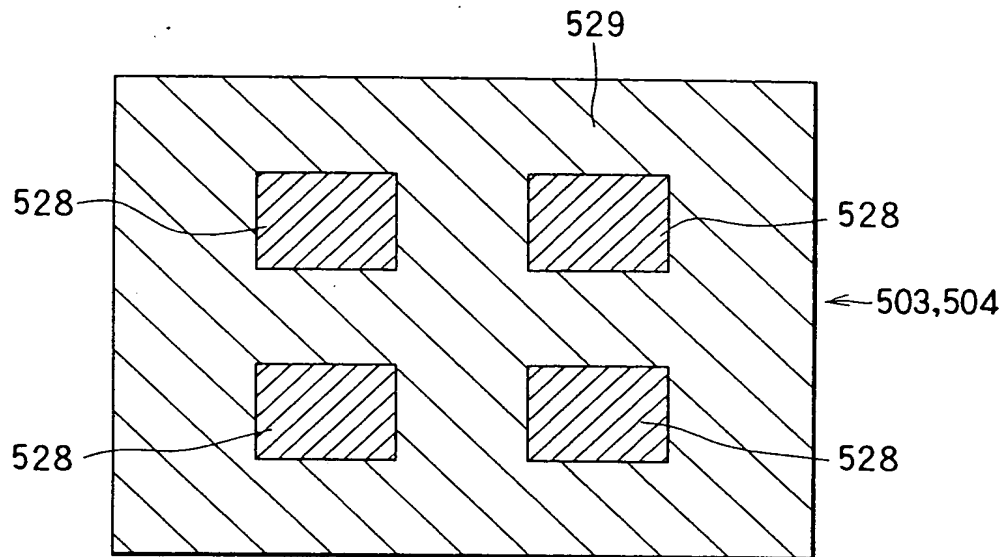


FIG. 35B

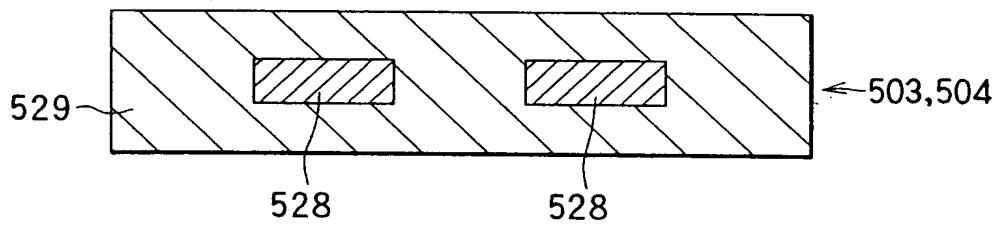


FIG. 36

